(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
27 August 2009 (27.08.2009)

PCT

(10) International Publication Number
WO 2009/104060 A1

(51) International Patent Classification:
H01L 21/762 (2006.01)

(21) International Application Number:
PCT/IB2008/051801

(22) International Filing Date:
20 February 2008 (20.02.2008)

(25) Filing Language: English

(26) Publication Language: English

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

— *of inventorship (Rule 4.17(iv))*

Published:

— *with international search report (Art. 21(3))*

(54) Title: OXIDATION AFTER OXIDE DISSOLUTION

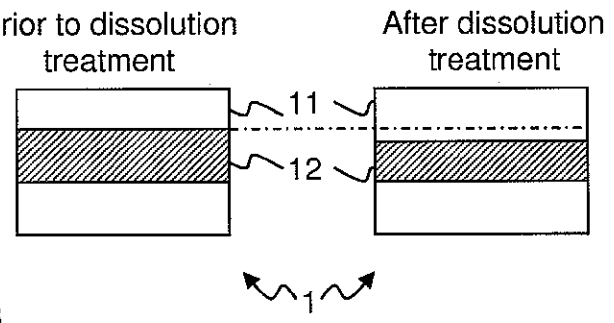


FIG. 3

(57) Abstract: 13 Abstract Method for manufacturing a SeOI substrate (1) with a thin buried oxide, said substrate comprising: -a thin working layer (11) made from one or more semiconductor material(s); -a support layer; and -a thin buried oxide layer (12) between the working layer and the support layer; said method comprising: -a manufacturing step of an intermediate SeOI substrate having a buried oxide layer with a thickness greater than a thickness desired for said thin buried oxide layer; -a dissolution step of said buried oxide layer (12) in order to form therewith said thin buried oxide layer; characterized in that the method comprises after said dissolution step an oxidation step of said substrate for creating an oxidized layer (13) on the substrate, and an oxide migration step for diffusing at least a part of said oxide layer through the working layer, in order to increase the electrical interface quality of said substrate and decrease its Dit value.

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